Customer No.: 31561
Application No.: 10/064,766
Docket NO.:8043-US-PA

Claim Amendment

Please amend the claims according to the following listing of claims and substitute it for all prior versions and listings of claims in the application.

1. (original) A method for decreasing a number of particles during an etching process of a material layer in which a wafer is put on a susceptor in an etching chamber, comprising:

setting a height of the susceptor and performing an etching process at such a height;

measuring deviations of etching depth at different locations under such a height;

repeating the above two steps with respect to various heights so as to obtain several sets of corresponding data for different heights; and

selecting the height resulting in a minimum deviation of etching depth as a height to perform a normal etching process.

2. (original)The method of claim 1, wherein the height of the wafer is adjusted with a shaft under the susceptor, the shaft being capable of moving up and down to drive the susceptor vertically.

3. (original)The method of claim 1, wherein the material layer comprises silicon oxide.

4. (original) The method of claim 1, wherein the material layer is a dielectric layer, the etching chamber is a part of a metal deposition machine, and the etching process is for rounding a corner of an opening in the dielectric layer.

Claims 5-7 (cancelled)

8. (original) A method for rounding a corner of an opening in a dielectric layer on a substrate, comprising:

loading the substrate on a susceptor in an etching chamber; and

performing a corner-rounding etching process to round the corner of the opening in the dielectric layer with a height of the substrate in the etching chamber being adjusted to an optimum height that results in a minimum deviation of etching depth of the dielectric layer in the corner-rounding etching process.

9. (original) The method of claim 8, wherein the height of the substrate is adjusted with a shaft under the susceptor, the shaft being capable of moving up and down to drive the susceptor vertically.

10. (original) The method of claim 8, wherein the dielectric layer comprises silicon oxide.